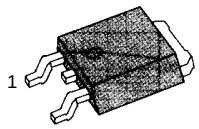
KSH210 PNP EPITAXIAL SILICON TRANSISTOR

D-PACK FOR SURFACE MOUNT APPLICATIONS

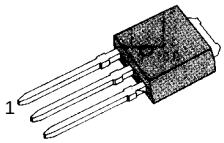
- High DC Current Gain
- Low Collector Emitter Saturation Voltage
- Lead Formed for Surface Mount Applications (No Suffix)
- Straight Lead (I. PACK, " - I " Suffix)

D-PAK



1. Base 2. Collector 3. Emitter

I-PAK



1. Base 2. Collector 3. Emitter

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	- 40	V
Collector Emitter Voltage	V_{CEO}	- 25	V
Emitter Base Voltage	V_{EBO}	- 8	V
Base Current	I_C	- 1	A
Collector Current (DC)	I_C	- 5	A
Collector Peck Current (Pulse)	I_B	- 10	A
Collector Dissipation (T_A = 25℃)	P_C	1.4	W
Collector Dissipation (T_C = 25℃)	P_C	12.5	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-65 ~ 150	℃

ELECTRICAL CHARACTERISTICS (Tc =25℃)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
*Collector Emitter Sustaining Voltage	V_{CEO} (sus)	I_C = - 10mA, I_B = 0	-25		V
Collector Cutoff Current	I_{CBO}	V_{CB} = - 40V, I_E = 0		-100	nA
Emitter Cutoff Current	I_{EBO}	V_{EBO} = - 8V, I_C = 0		-100	nA
* DC Current Gain	h_{FE}	V_{CE} = - 1V, I_C = - 500mA	70		
		V_{CE} = - 1V, I_C = - 2A	45	180	
		V_{CE} = - 2V, I_C = - 5A	10		
* Collector Emitter Saturation Voltage	V_{CE}(sat)	I_C = - 500mA, I_B= - 50mA		-0.3	V
		I_C = - 2A, I_B = - 200mA		-0.75	V
		I_C = - 5A, I_B = - 1A		-1.8	V
* Base Emitter Saturation Voltage	V_{BE}(sat)	I_C = - 5A, I_B = - 1A		-2.5	V
* Base Emitter On Voltage	V_{BE}(on)	V_{CE} = - 1V, I_C = - 2A		-1.6	V
Current Gain Bandwidth Product	f_T	V_{CE} = - 10V, I_C = - 100mA, f = 10MHz	65		MHz
Output Capacitance	C_{OB}	V_{CB} = - 10V, I_E = 0, f = 0.1MHz		120	pF

* Pulse Test : PW ≤ 300uS, Duty Cycle ≤ 2%

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